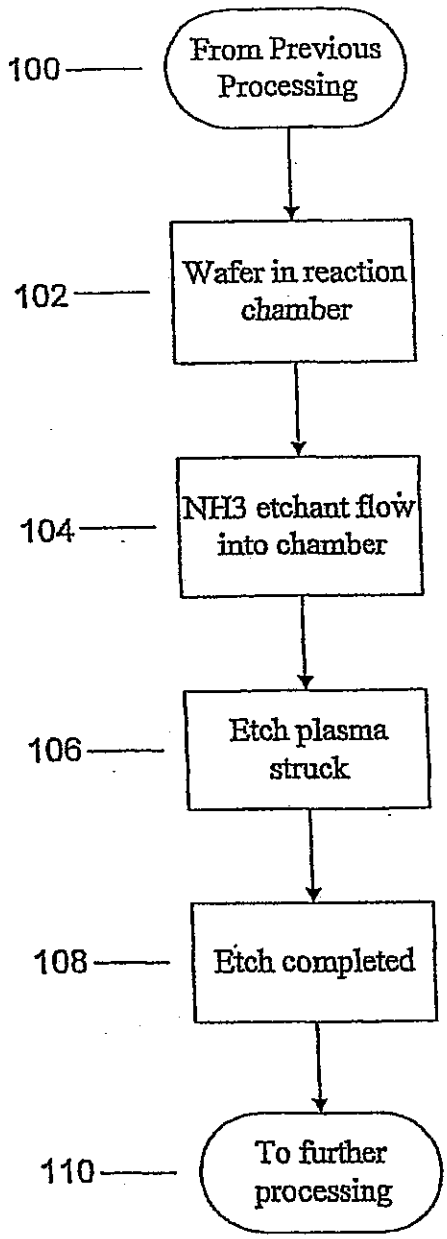

100
From Previous Processing
102
Wafer in reaction chamber
104
NH3 etchant flow into chamber
106
Etch plasma struck
108
Etch completed
110
To further processing

Fig. 1a

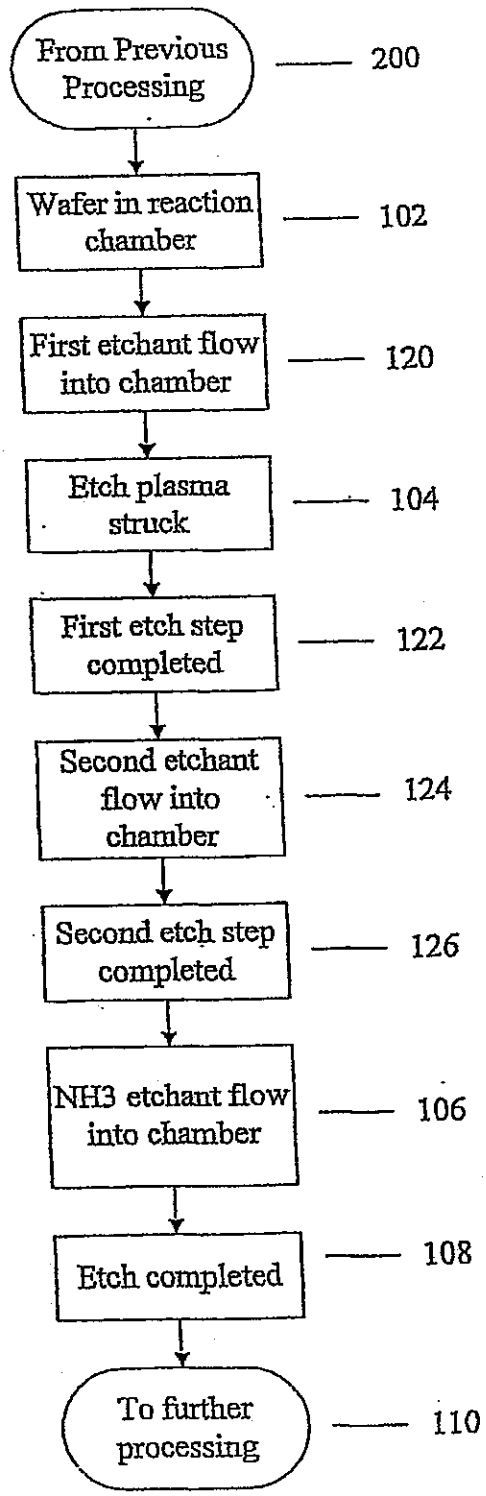

From Previous Processing
200
Wafer in reaction chamber
102
First etchant flow into chamber
120
Etch plasma struck
104
First etch step completed
122
Second etchant flow into chamber
124
Second etch step completed
126
NH3 etchant flow into chamber
106
Etch completed
108
To further processing
110

Fig. 1b

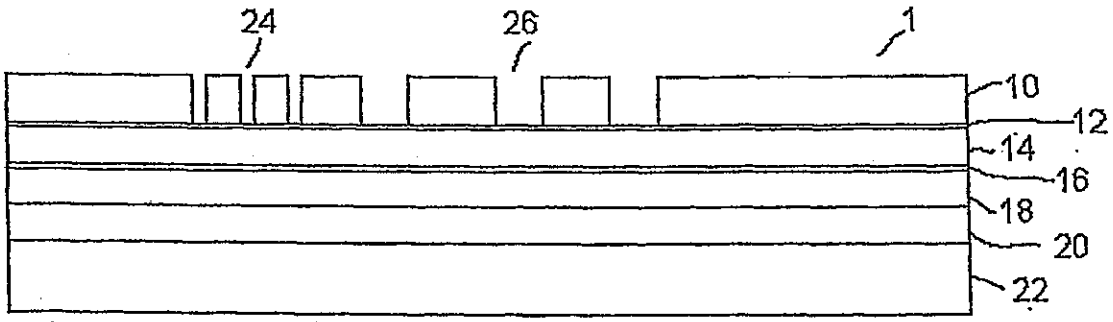


Fig. 2a

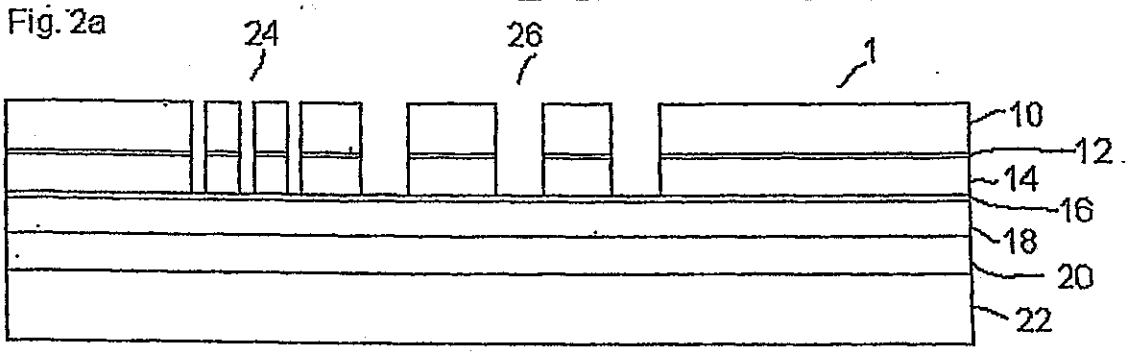


Fig. 2b

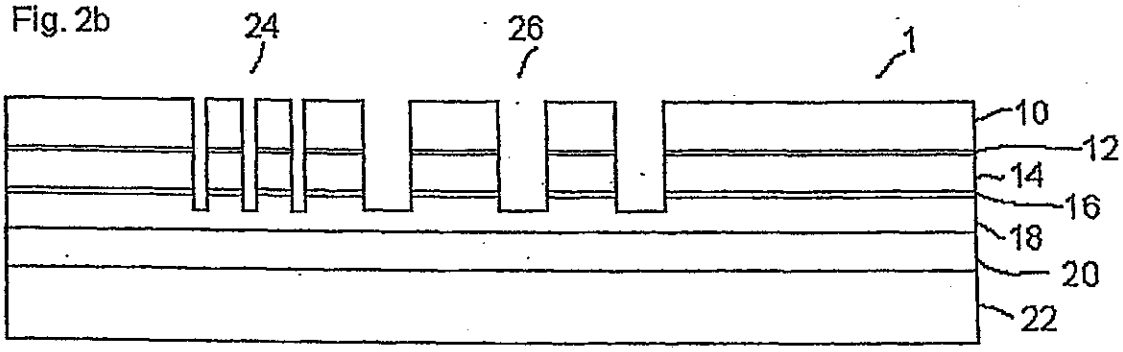


Fig. 2c

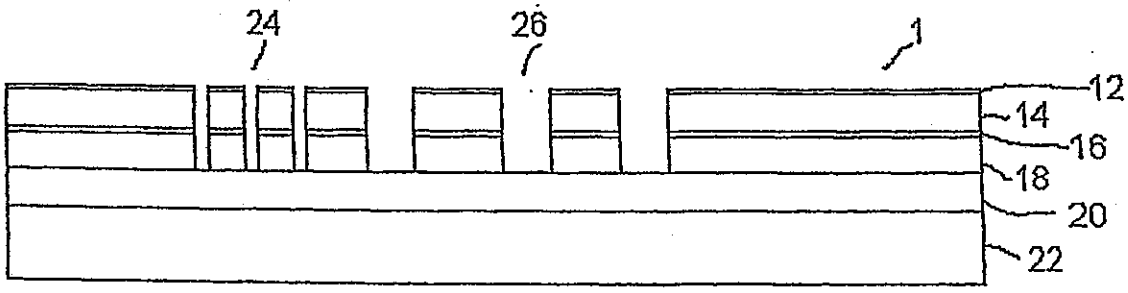


Fig. 2d

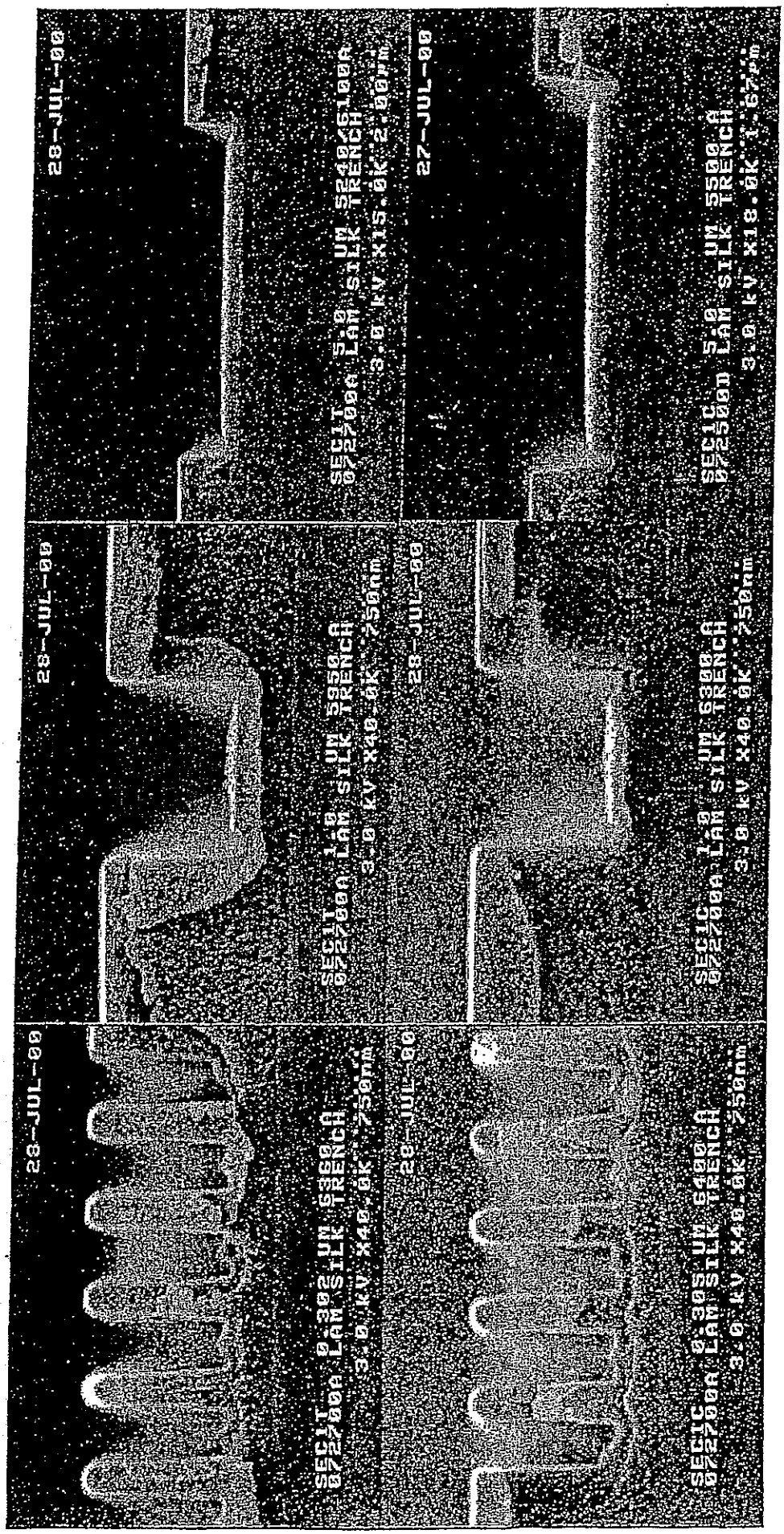

28-JUL-00
SEC1T 0.302 UM 6300 A
0727000 LAM SiLK TRENCH
3.0 kV X40.0K .750nm
28-JUL-00
SEC1C 0.305 UM 6400 A
0727000 LAM SiLK TRENCH
3.0 kV X40.0K .750nm
28-JUL-00
SEC1I 1.0 UM 5300 A
0727000 LAM SiLK TRENCH
3.0 kV X40.0K .750nm
28-JUL-00
SEC1C 1.0 UM 6300 A
0727000 LAM SiLK TRENCH
3.0 kV X40.0K .750nm
28-JUL-00
SEC1T 5.0 UM 5240 A
0727000 LAM SiLK TRENCH
3.0 kV X15.0K 2.00mm
27-JUL-00
SEC1C 5.0 UM 5500 A
0725000 LAM SiLK TRENCH
3.0 kV X18.0K 1.67mm

FIG. 3